

RJK1526DPJ, RJK1526DPE, RJK1526DPF

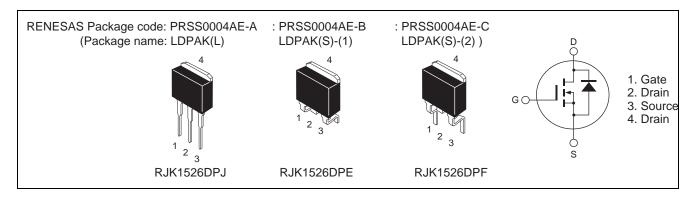
Silicon N Channel MOS FET High Speed Power Switching

REJ03G1859-0100 Rev.1.00 Nov 06, 2009

Features

- Low on-resistance $R_{DS(on)}=0.036~\Omega~typ.~(at~I_D=25~A,~V_{GS}=10~V,~Ta=25^{\circ}C)$
- Low leakage current
- High speed switching

Outline



Absolute Maximum Ratings

 $(Ta = 25^{\circ}C)$

| Item | Symbol | Ratings | (1a = 23 C) |
|---|------------------------------|-------------|-------------|
| Drain to source voltage | V _{DSS} | 150 | V |
| Gate to source voltage | V _{GSS} | ±30 | V |
| Drain current | I _D | 50 | Α |
| Drain peak current | I _{D (pulse)} Note1 | 120 | Α |
| Body-drain diode reverse drain current | I _{DR} | 50 | Α |
| Body-drain diode reverse drain peak current | I _{DR} (pulse) | 120 | Α |
| Avalanche current | I _{AP} Note3 | 25 | Α |
| Avalanche energy | E _{AR} Note3 | 46.8 | mJ |
| Channel dissipation | Pch Note2 | 100 | W |
| Channel to case thermal impedance | θch-c | 1.25 | °C/W |
| Channel temperature | Tch | 150 | °C |
| Storage temperature | Tstg | -55 to +150 | °C |

Notes: 1. PW \leq 10 μ s, duty cycle \leq 1%

- 2. Value at Tc = 25°C
- 3. STch = 25° C, Tch $\leq 150^{\circ}$ C

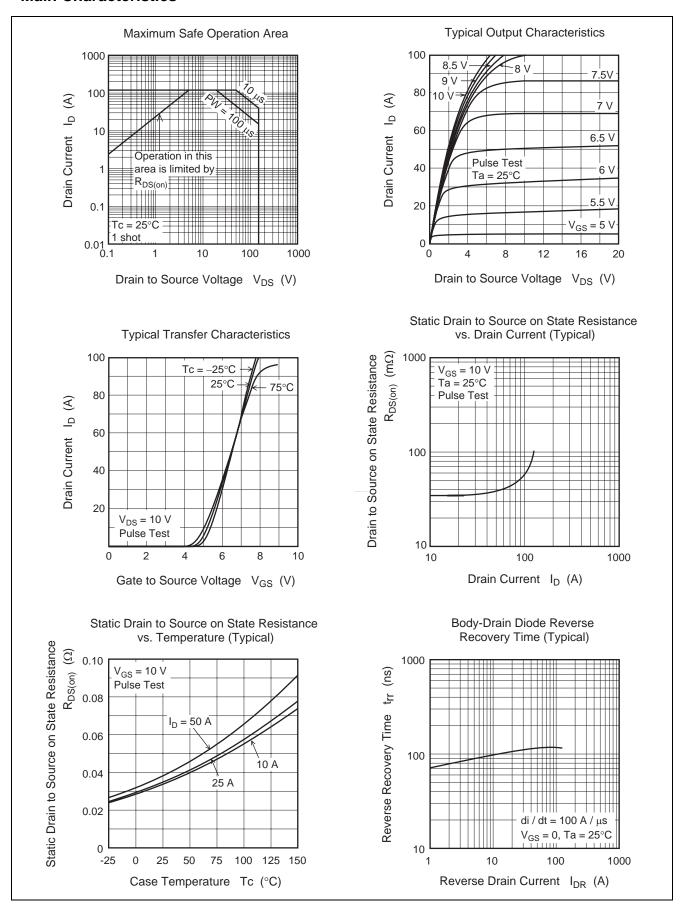
Electrical Characteristics

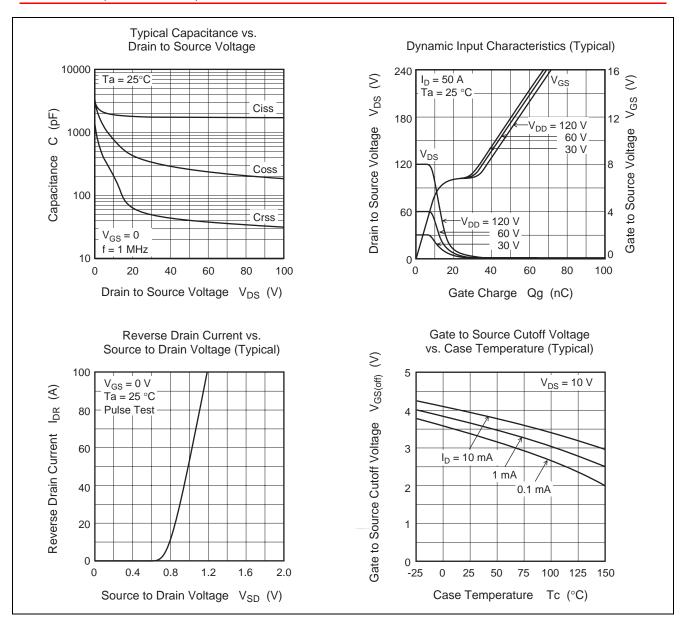
 $(Ta = 25^{\circ}C)$

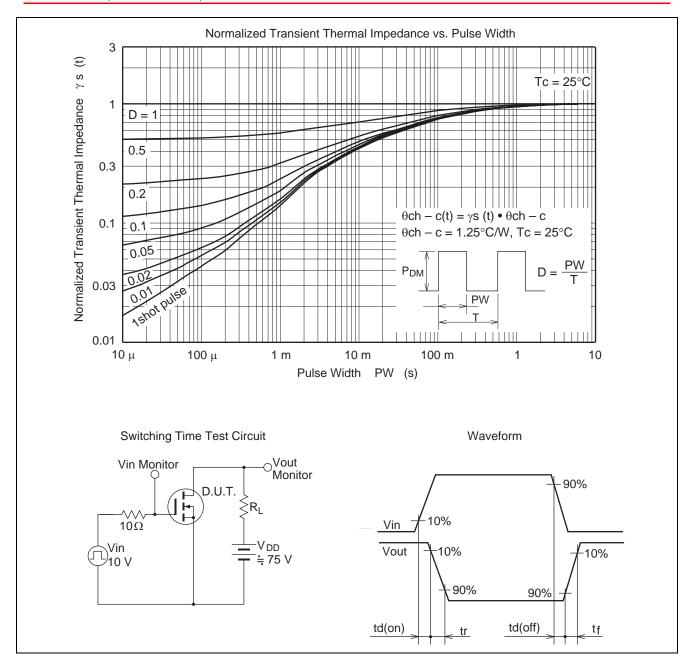
| Item | Symbol | Min | Тур | Max | Unit | Test conditions |
|--|---------------------|-----|-------|-------|------|--|
| Drain to source breakdown voltage | $V_{(BR)DSS}$ | 150 | _ | _ | V | $I_D = 10 \text{ mA}, V_{GS} = 0$ |
| Zero gate voltage drain current | I _{DSS} | _ | _ | 1 | μΑ | $V_{DS} = 150 \text{ V}, V_{GS} = 0$ |
| Gate to source leak current | I _{GSS} | _ | _ | ±0.1 | μΑ | $V_{GS} = \pm 30 \text{ V}, V_{DS} = 0$ |
| Gate to source cutoff voltage | $V_{GS(off)}$ | 3.0 | _ | 4.5 | V | $V_{DS} = 10 \text{ V}, I_{D} = 1 \text{ mA}$ |
| Static drain to source on state resistance | R _{DS(on)} | _ | 0.036 | 0.042 | Ω | $I_D = 25 \text{ A}, V_{GS} = 10 \text{ V}^{Note4}$ |
| Input capacitance | Ciss | _ | 1800 | _ | pF | V _{DS} = 25 V |
| Output capacitance | Coss | _ | 380 | _ | pF | $V_{GS} = 0$ |
| Reverse transfer capacitance | Crss | _ | 56 | _ | pF | f = 1 MHz |
| Turn-on delay time | t _{d(on)} | _ | 35 | _ | ns | I _D = 25 A |
| Rise time | t _r | _ | 141 | _ | ns | V _{GS} = 10 V |
| Turn-off delay time | $t_{d(off)}$ | _ | 86 | _ | ns | $R_L = 3 \Omega$ |
| Fall time | t _f | _ | 15 | _ | ns | $Rg = 10 \Omega$ |
| Total gate charge | Qg | _ | 46 | _ | nC | V _{DD} = 120 V |
| Gate to source charge | Qgs | _ | 12 | _ | nC | V _{GS} = 10 V |
| Gate to drain charge | Qgd | _ | 21 | _ | nC | I _D = 50 A |
| Body-drain diode forward voltage | V_{DF} | _ | 1.0 | 1.5 | V | $I_F = 50 \text{ A}, V_{GS} = 0^{\text{Note4}}$ |
| Body-drain diode reverse recovery time | t _{rr} | _ | 120 | _ | ns | $I_F = 50 \text{ A}, V_{GS} = 0$ di _F /dt = 100 A/ μ s |

Notes: 4. Pulse test

Main Characteristics

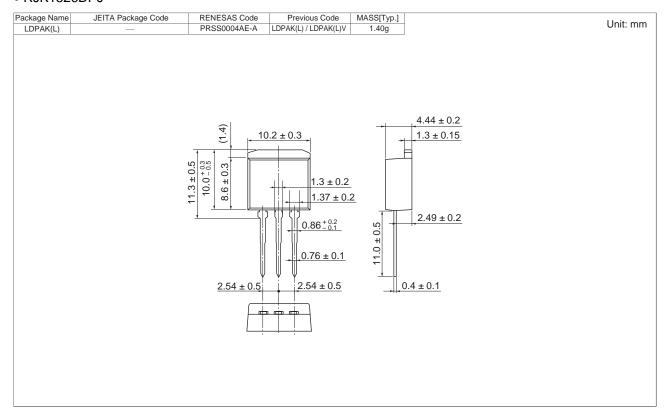




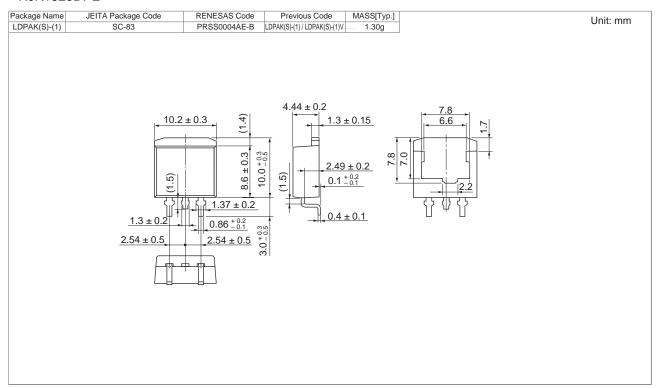


Package Dimensions

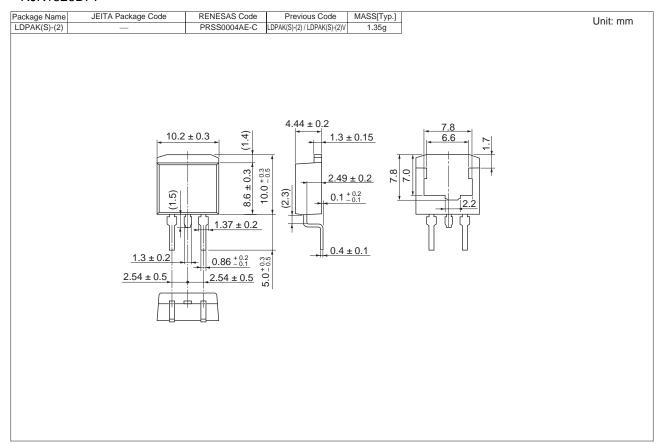
• RJK1526DPJ



• RJK1526DPE



• RJK1526DPF



Ordering Information

| Part Name | Quantity | Shipping Container |
|---------------|----------|--------------------|
| RJK1526DPE-J3 | 1000 pcs | Taping |

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